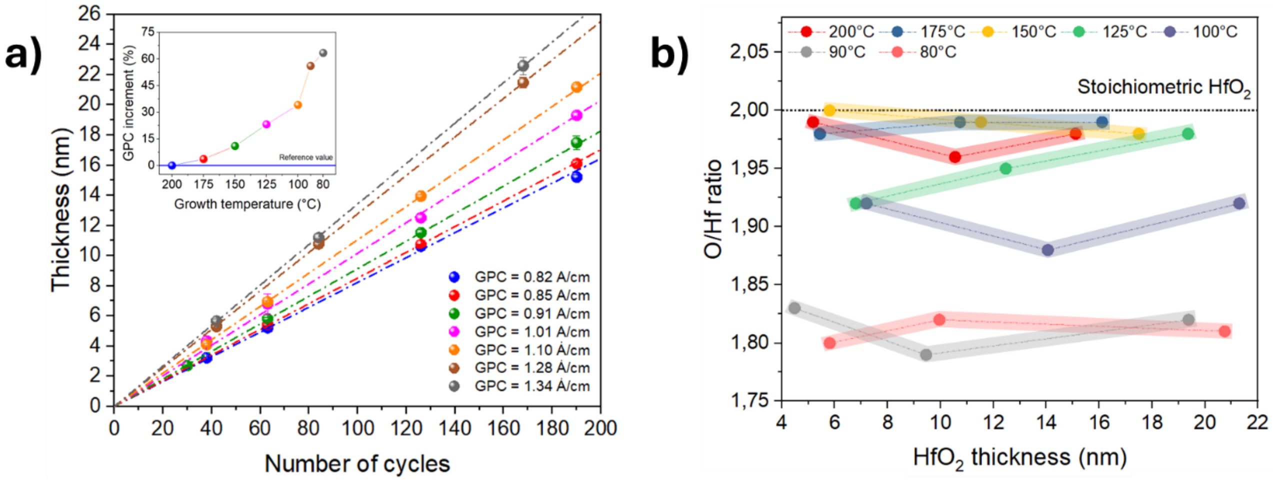

Figure 1 – Panels a) and b) show, respectively, the extrapolated GPC of ALD HfO$_2$ growths from 200 °C to 80 °C and stoichiometry (O/Hf ratio) for different HfO$_2$ thicknesses over the investigated temperature range.

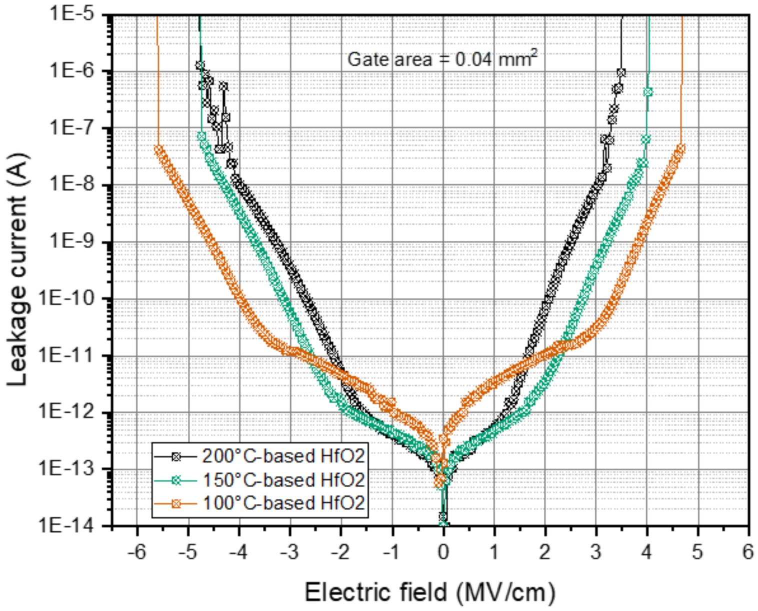

Figure 2 – I-E curves from MIM devices integrating 10 nm of 100, 150 and 200 °C-based ALD HfO$_2$